PROCEEDINGS OF SPIE

Advanced Etch Technology for Nanopatterning VIII

Richard S. Wise Catherine B. Labelle Editors

25–26 February 2019 San Jose, California, United States

Sponsored by SPIE

Cosponsored by LAM Research Corporation (United States)

Published by SPIE

Volume 10963

Proceedings of SPIE 0277-786X, V. 10963

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Advanced Etch Technology for Nanopatterning VIII, edited by Richard S. Wise, Catherine B. Labelle, Proc. of SPIE Vol. 10963, 1096301 · © 2019 SPIE · CCC code: 0277-786X/19/\$18 · doi: 10.1117/12.2533873

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Author(s), "Title of Paper," in Advanced Etch Technology for Nanopatterning VIII, edited by Richard S. Wise, Catherine B. Labelle, Proceedings of SPIE Vol. 10963 (SPIE, Bellingham, WA, 2019) Seven-digit Article CID Number.

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510625730

ISBN: 9781510625747 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445

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